L Number	Hits	Search Text	DB	Time stamp
1	8	(("6114230") or ("6074939") or ("6037228") or ("6001541") or ("5759916") or ("5733712") or ("5554486") or ("5545588")).PN.	USPAT; US-PGPUB	2004/05/05 10:29
2	4	((("6114230") or ("6074939") or ("6037228") or ("6001541") or ("5759916") or ("5733712") or ("5554486") or ("5545588")).PN.) and ARC	USPAT; US-PGPUB	2004/05/05 10:27
3	3	(((("6114230") or ("6074939") or ("6037228") or ("6001541") or ("5759916") or ("5733712") or ("5554486") or ("5545588")).PN.) and ARC) and plasma	USPAT; US-PGPUB	2004/05/05 10:27
4	192	ARC with SiON	USPAT; US-PGPUB	2004/05/05 10:30
5	0	(ARC with SiON) same (resistance with (oxygen or "O.sub.2"))	USPAT; US-PGPUB	2004/05/05 10:31
6	33	(ARC with SiON) same ((oxygen or "O.sub.2"))	USPAT; US-PGPUB	2004/05/05 10:31
7	31	((ARC with SiON) same ((oxygen or "O.sub.2"))) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 10:38
8	11	(((ARC with SiON) same ((oxygen or "O.sub.2"))) and @ad<20020219) and (low with (k or dielectric))	USPAT; US-PGPUB	2004/05/05 10:36
9	1	(ARC with SiON) same (resistance or resistant) same (oxygen or "O.sub.2")	USPAT; US-PGPUB	2004/05/05 10:38
10	18	(ARC with SiON) and ((resistance or resistant) same (oxygen or "O.sub.2"))	USPAT; US-PGPUB	2004/05/05 10:43
11	15	((ARC with SiON) and ((resistance or resistant) same (oxygen or "O.sub.2"))) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 10:43
12	0	(ARC with SiON) and ((resistance or resistant) same (oxygen or "O.sub.2"))	EPO; JPO; DERWENT; IBM_TDB	2004/05/05 10:43
13	0	(ARC with SiON) and (resist same (oxygen or "O.sub.2"))	EPO; JPO; DERWENT; IBM_TDB	2004/05/05 10:43
14	31	(ARC with SiON) and (resist same (oxygen or "O.sub.2"))	USPAT; US-PGPUB	2004/05/05 10:43
15	26	((ARC with SiON) and (resist same (oxygen or "O.sub.2"))) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 11:48
16	1382	ARC and (low with (k or dielectric))and (resist or mask or photoresist)	USPAT; US-PGPUB	2004/05/05 11:48
17	3	(ARC and (low with (k or dielectric))and (resist or mask or photoresist)) and (polymer with (wet near3 etching))	USPAT; US-PGPUB	2004/05/05 11:58
18	3	((ARC and (low with (k or dielectric))and (resist or mask or photoresist)) and (polymer with (wet near3 etching))) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 11:49
19	5	(ARC and (low with (k or dielectric))and (resist or mask or photoresist)) and ((organic or residue) with (wet near3 etching))	USPAT; US-PGPUB	2004/05/05 11:49
20	5	((ARC and (low with (k or dielectric))and (resist or mask or photoresist)) and ((organic or residue) with (wet near3 etching))) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 11:58
21	12	(ARC and (low with (k or dielectric))and (resist or mask or photoresist)) and (cleaning with (wet near3 etching))	USPAT; US-PGPUB	2004/05/05 11:58
22	8	((ARC and (low with (k or dielectric))and (resist or mask or photoresist)) and (cleaning with (wet near3 etching))) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 12:47
23	627471	(organic or (low adj (K or dielectric)))	USPAT; US-PGPUB	2004/05/05 12:45
24	3491	(low adj (K or dielectric)) same (trench or via or opening or hole or aperture or recess)	USPAT; US-PGPUB	2004/05/05 12:46

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25	299	((low adj (K or dielectric)) same (trench or via or opening or hole or aperture or recess)) and arc	USPAT; US-PGPUB	2004/05/05 12:46
26	231	(((low adj (K or dielectric)) same (trench or via or opening or hole or aperture or recess)) and arc) and (resist or photoresist or photomask)	USPAT; US-PGPUB	2004/05/05 12:47
27	89	((((low adj (K or dielectric)) same (trench or via or opening or hole or aperture or recess)) and arc) and (resist or photoresist or photomask)) and (precleaning or cleaning or clean or preclean)	USPAT; US-PGPUB	2004/05/05 12:47
28	55	(((((low adj (K or dielectric)) same (trench or via or opening or hole or aperture or recess)) and arc) and (resist or photoresist or photomask)) and (precleaning or cleaning or clean or preclean)) and @ad<20020219	USPAT; US-PGPUB	2004/05/05 12:54
29	23	((((((low adj (K or dielectric)) same (trench or via or opening or hole or aperture or recess)) and arc) and (resist or photoresist or photomask)) and (precleaning or cleaning or clean or preclean)) and @ad<20020219) and wet	USPAT; US-PGPUB	2004/05/05 12:54